

Single N-Channel, 60V, 340mA, MOSFET

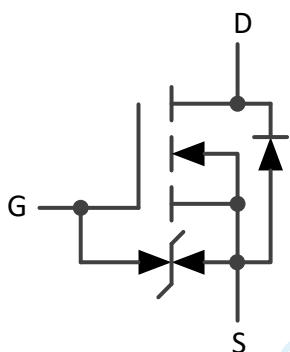
Features

- ✧ High density cell design for Low $R_{DS(on)}$
- ✧ Voltage controlled small signal switch
- ✧ Rugged and reliable
- ✧ ESD protected Gate HBM 2.5kV

V_{DS} (V)	Typical $R_{DS(on)}$ (Ω)
60	1.3 @ $V_{GS}=10V$
	1.4 @ $V_{GS}=4.5V$

Applications

- ✧ DC/DC Converter
- ✧ Load Switch for Portable Devices
- ✧ Battery Switch



Circuit Diagram

Mechanical Data

- ✧ UL Flame Rating : UL94V-0
- ✧ Reel Size : 7 inch
- ✧ RoHS/WEEE Compliant



SOT-723

Absolute Maximum Rating at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	340	mA
Power Dissipation	P_D	0.15	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}\text{C}$

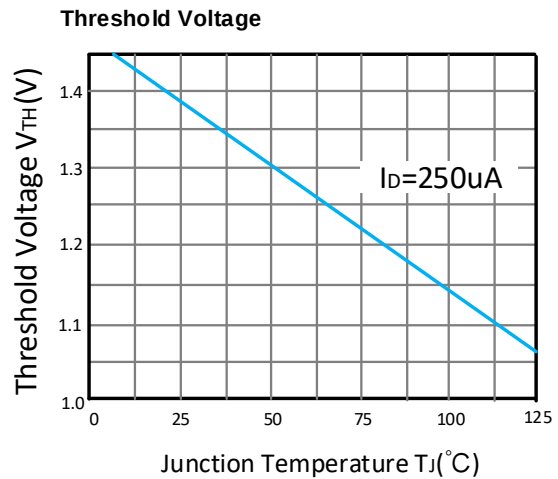
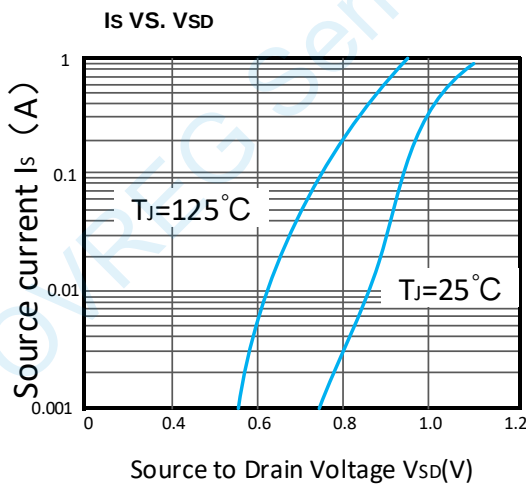
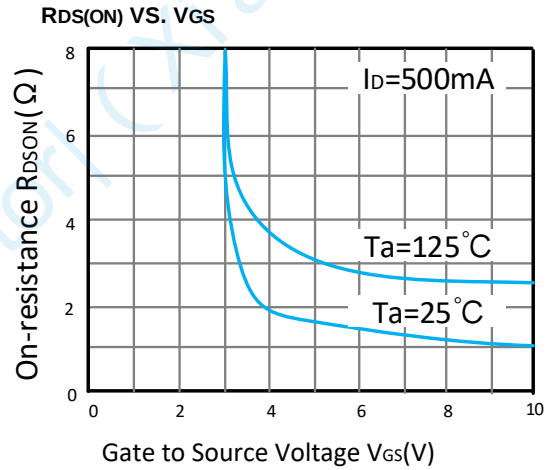
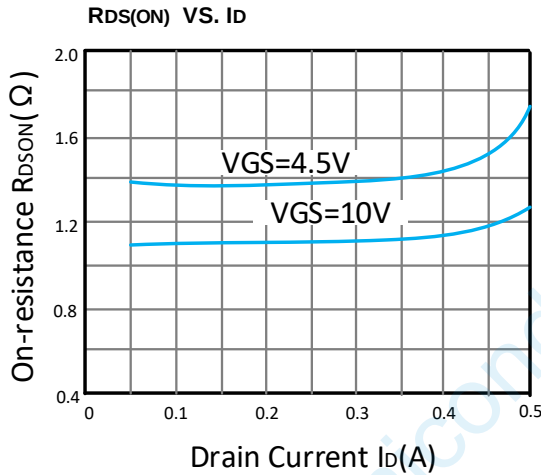
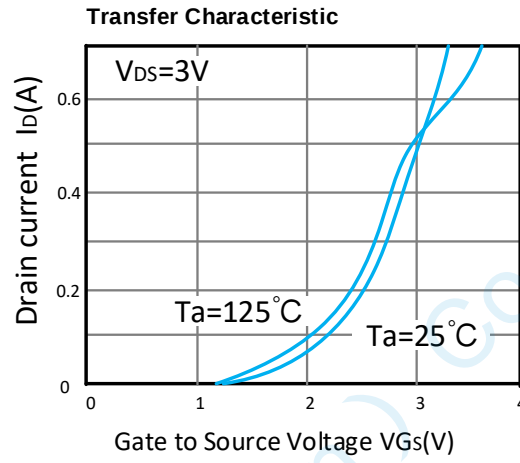
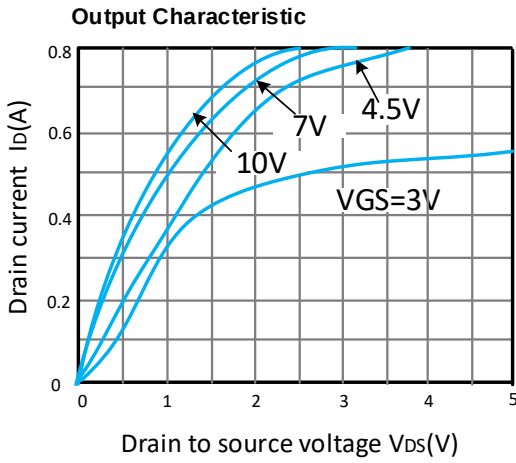
Electrical Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 48V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS1}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 10	μA
	I_{GSS2}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 200	nA
	I_{GSS2}	$V_{GS} = \pm 5V, V_{DS} = 0V$			± 100	nA
Gate threshold voltage*	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.1	1.4	1.7	V
Drain-source on-resistance*	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 500mA$		1.3	4.0	Ω
		$V_{GS} = 4.5V, I_D = 200mA$		1.4	4.5	
Recovered charge	Q_r	$V_{GS} = 0V, I_S = 300mA, V_R = 25V, dl_s/dt = -100A/\mu S$		30		nC
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$			40	pF
Output Capacitance	C_{oss}				30	
Reverse Transfer Capacitance	C_{rss}				10	
Switching Characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 10V, V_{DD} = 50V, R_G = 50\Omega, R_{GS} = 50\Omega, R_L = 250\Omega$			10	ns
Turn-off delay time	$t_{d(off)}$				15	
Reverse recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 300mA, V_R = 25V, dl_s/dt = -100A/\mu S$		30		
Source-Drain Diode characteristics						
Diode Forward voltage	V_{SD}	$V_{GS} = 0V, I_S = 300mA$		0.97	1.5	V
GATE-SOURCE ZENER DIODE						
Gate-Source Breakdown Voltage	BV_{GSO}	$I_{GS} = \pm 1mA$ (Open Drain)	± 21.5		± 30	V

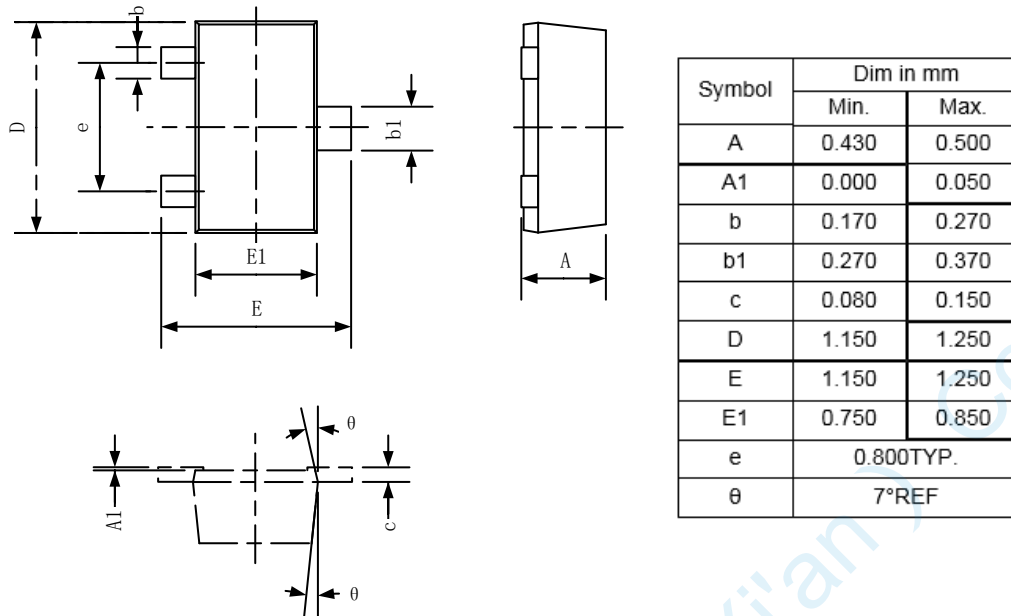
Notes:

*Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

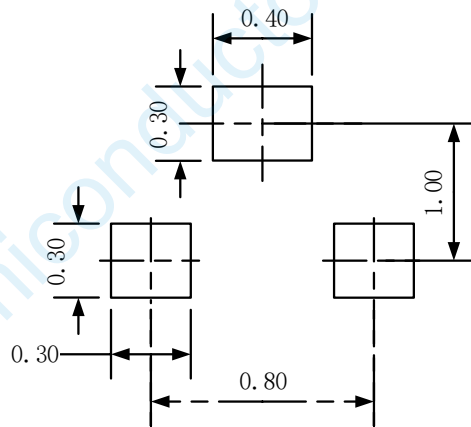
Typical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified



Package Information

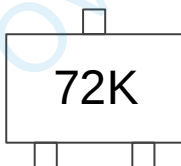


Recommend PCB Layout



Notes: This PCB Layout Is For Reference Purposes Only

Marking



Ordering Information

Part number	Material	Type	Reel size	MOQ	MOQ/internal box	MOQ/carton
OVM6013ET7	GREEN	T/R	7 inch	10k/reel	10reel= 100k/box	4boxes=400k/carton